



## UF50N06-Q

Preliminary

Power MOSFET

### 50A, 60V N-CHANNEL POWER MOSFET

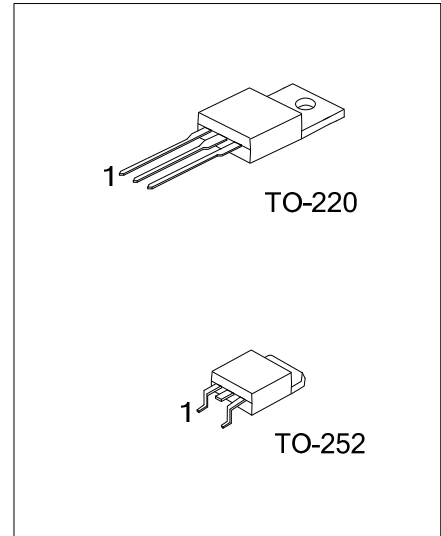
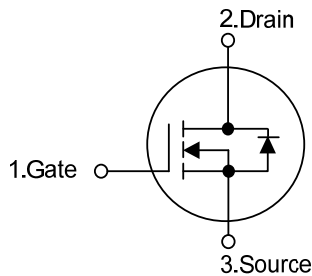
#### DESCRIPTION

The UTC **UF50N06-Q** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

#### FEATURES

- \*  $R_{DS(ON)} < 25m\Omega @ V_{GS}=10V, I_D=25A$
- \* High switching speed
- \* 100% avalanche tested

#### SYMBOL



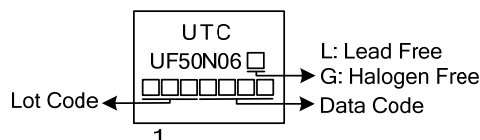
#### ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UF50N06L-TA3-T	UF50N06G-TA3-T	TO-220	G	D	S	Tube
UF50N06L-TN3-R	UF50N06G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>UF50N06G-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TN3: TO-252 (3) G: Halogen Free and Lead Free L: Lead Free</p>
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#### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 25$	V
Continuous Drain Current	Continuous	$I_D$	50
	Pulsed	$I_{DM}$	200
Avalanche Energy	$E_{AS}$	287	mJ
Peak Diode Recovery dv/dt (Note 4)	dv/dt	12.6	V/ns
Power Dissipation	TO-220	$P_D$	80
	TO-252		50
Junction Temperature	$T_J$	+150	$^\circ\text{C}$
Storage Temperature Range	$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L=0.38\text{mH}$ ,  $I_{AS}=38\text{A}$ ,  $V_{DD}=50\text{V}$ ,  $R_G=25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 50\text{A}$ ,  $di/dt \leq 250\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	$\theta_{JA}$	62.5
	TO-252		110
Junction to Case	TO-220	$\theta_{JC}$	1.56
	TO-252		2.5

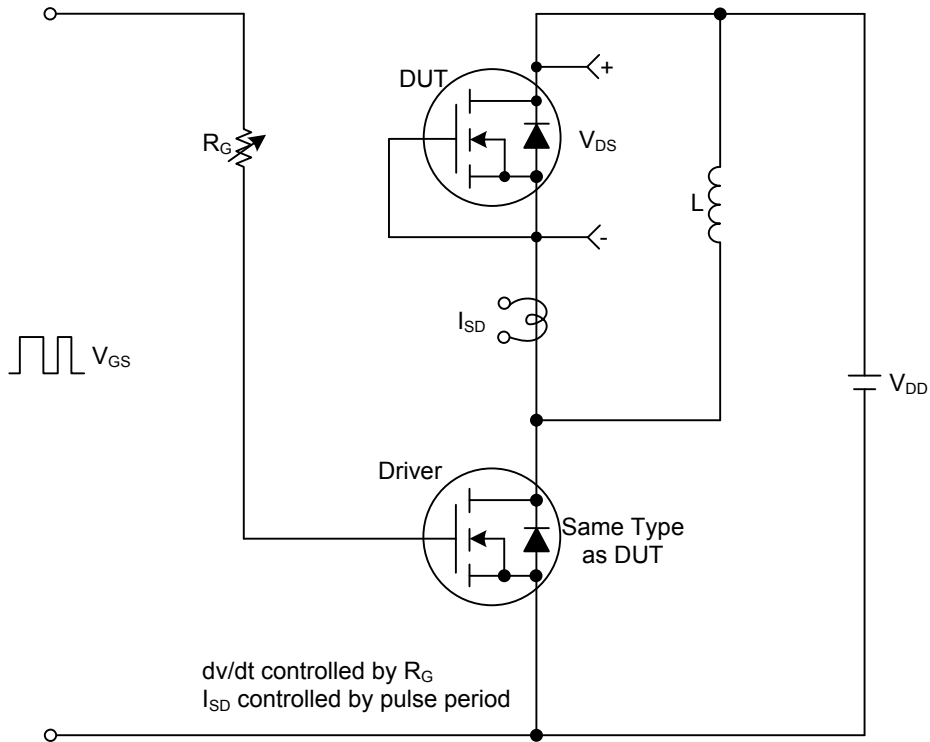
■ ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu\text{A}$ , $V_{GS} = 0\text{V}$	60			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 60\text{V}$ , $V_{GS} = 0\text{V}$			1	$\mu\text{A}$
Gate-Source Leakage Current	Forward	$V_{GS} = +20\text{V}$ , $V_{DS} = 0\text{V}$			10	$\mu\text{A}$
	Reverse		$V_{GS} = -20\text{V}$ , $V_{DS} = 0\text{V}$			-10
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$I_D = 250\mu\text{A}$ , $V_{DS} = V_{GS}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$ , $I_D = 25\text{A}$			25	m $\Omega$
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		1800		pF
Output Capacitance	$C_{OSS}$			390		pF
Reverse Transfer Capacitance	$C_{RSS}$			64		pF
<b>SWITCHING PARAMETERS</b>						
Total Gate Charge (Note 1)	$Q_G$	$V_{GS} = 10\text{V}$ , $V_{DS} = 50\text{V}$ , $I_D = 1.3\text{A}$ $I_G = 100\mu\text{A}$ (Note 1, 2)		63.6		nC
Gate to Source Charge	$Q_{GS}$			9.2		nC
Gate to Drain Charge	$Q_{GD}$			12		nC
Turn-ON Delay Time (Note 1)	$t_{D(ON)}$	$V_{GS} = 10\text{V}$ , $V_{DD} = 30\text{V}$ , $R_G = 25\Omega$ , $I_D = 0.5\text{A}$ (Note 1, 2)		78		ns
Rise Time	$t_R$			81		ns
Turn-OFF Delay Time	$t_{D(OFF)}$			340		ns
Fall-Time	$t_F$			162		ns
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	$I_S$				50	A
Maximum Body-Diode Pulsed Current	$I_{SM}$				200	A
Drain-Source Diode Forward Voltage (Note 1)	$V_{SD}$	$I_S = 20\text{A}$ , $V_{GS} = 0\text{V}$			1.4	V
Body Diode Reverse Recovery Time (Note 1)	$t_{rr}$	$I_S = 40\text{A}$ , $V_{GS} = 0\text{V}$		66		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$dI_F/dt = 100\text{A}/\mu\text{s}$		0.5		$\mu\text{C}$

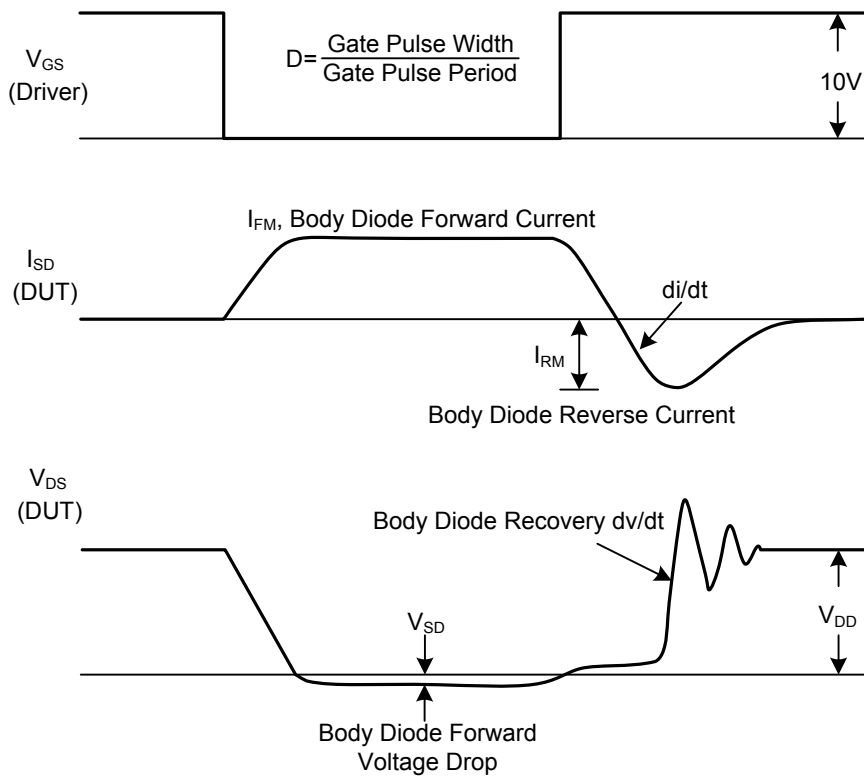
Notes: 1. Pulse Test: Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

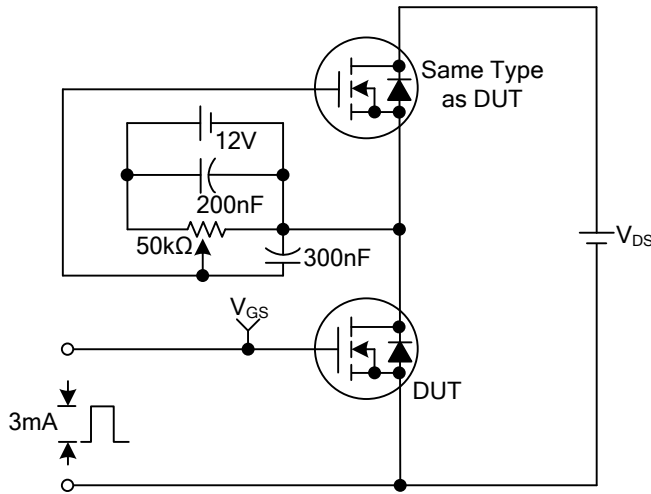


Peak Diode Recovery dv/dt Test Circuit

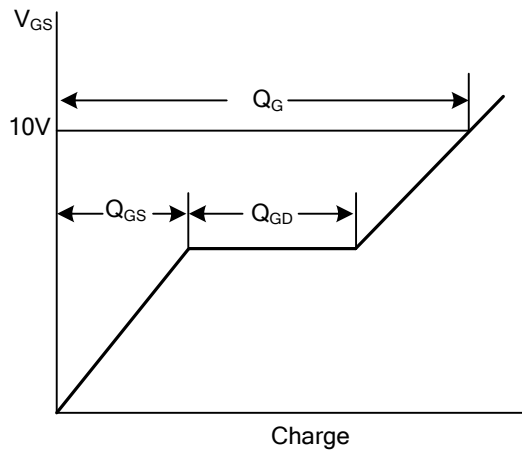


Peak Diode Recovery dv/dt Waveforms

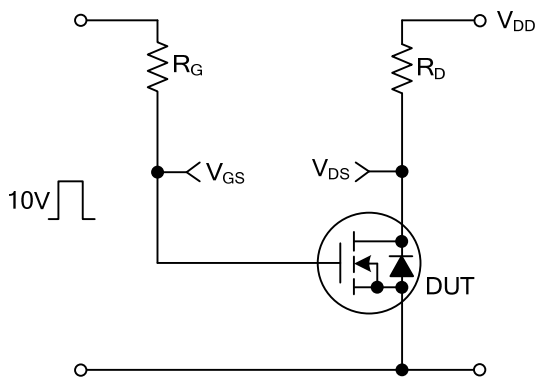
■ TEST CIRCUITS AND WAVEFORMS



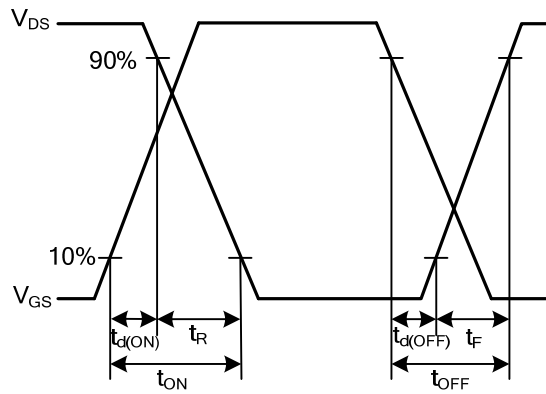
Gate Charge Test Circuit



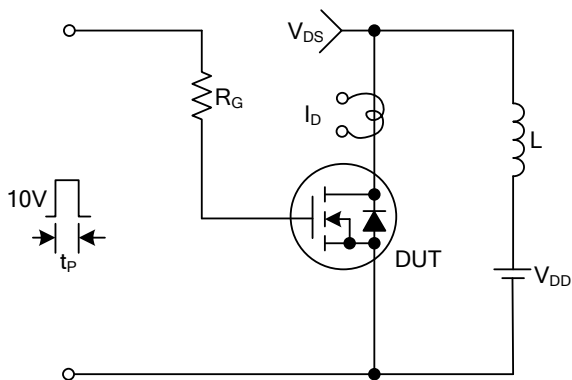
Gate Charge Waveforms



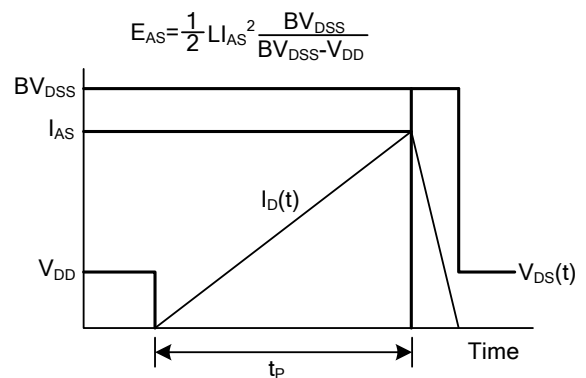
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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